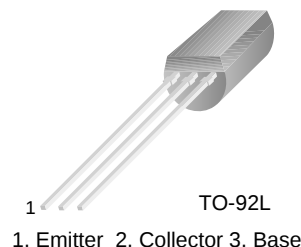


■■APPLICATION: High Voltage Applications.

■■MAXIMUM RATINGS (Ta=25℃)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V _{CBO}	-150	V
Collector-emitter voltage	V _{CEO}	-150	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current	I _C	-50	mA
Collector Power Dissipation	P _C	1	W
Junction Temperature	T _J	150	℃
Storage Temperature Range	T _{stg}	- 55~150	℃



■■ELECTRICAL CHARACTERISTICS (Ta=25℃)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h _{FE}	70		240		V _{CE} = -5V, I _C = -10mA
Collector Cut-off Current	I _{CBO}			-0.1	μA	V _{CB} = -150V, I _E =0
Emitter Cut-off Current	I _{EBO}			-0.1	μA	V _{EB} = -5V, I _C =0
Collector-Base Breakdown Voltage	BV _{CBO}	-150			V	I _C = -0.1mA, I _E =0
Collector-Emitter Breakdown Voltage	BV _{CEO}	-150			V	I _C = -1mA, I _B =0
Emitter-Base Breakdown Voltage	BV _{EBO}	-5			V	I _E = -0.1mA, I _C =0
Base-Emitter Voltage	V _{BE}			-0.9	V	V _{CE} = -5V, I _C = -30mA
Collector-Emitter Saturation Voltage	V _{CE(sat)}			-0.8	V	I _C = -10mA, I _B = -1mA
Gain bandwidth product	f _T		120		MHz	I _C = -10mA, V _{CE} = -30V
Common Base Output Capacitance	C _{ob}		4.0	5.0	PF	V _{CB} = -10V, I _E =0, f = 1MHz

■■hFE Classification

Classification	O	Y
h _{FE}	70~140	120~240